

B Vandana

List of Publications by Year in descending order

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papers

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2258059

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citing authors

#	ARTICLE	IF	CITATIONS
1	Inverted Si^{TM} Junctionless FinFET (ITJL FinFET): Performance Estimation through Device Geometry Variation. ECS Journal of Solid State Science and Technology, 2018, 7, Q52-Q59.	1.8	7
2	Memoryless nonlinearity in ITJL FinFET with spacer technology: Investigation towards reliability. Microelectronics Reliability, 2021, 119, 114072.	1.7	5
3	Impact of channel engineering ($\text{Si}_{1-0.25}\text{Ge}_{0.25}$) technique on G_m (transconductance) and its higher order derivatives of 3D conventional and wavy Junctionless FinFETs (JL). Facta Universitatis - Series Electronics and Energetics, 2018, 31, 257-265.	0.9	4
4	Mole Fraction Dependency Electrical Performances of Extremely Thin SiGe on Insulator Junctionless Channel Transistor (SG-OI JLCT). Lecture Notes in Electrical Engineering, 2019, , 573-581.	0.4	3
5	Effectiveness of High Permittivity Spacer for Underlap Regions of Wavy-Junctionless FinFET at 22Ånm Node and Scaling Short Channel Effects. Communications in Computer and Information Science, 2017, , 545-556.	0.5	2
6	Automatic movable road divider using Arduino UNO with Node Micro Controller Unit (MCU). Materials Today: Proceedings, 2021, , .	1.8	2
7	Exploration towards electrostatic integrity for SiGe on insulator (SG-OI) on junctionless channel transistor (JLCT). Facta Universitatis - Series Electronics and Energetics, 2017, 30, 383-390.	0.9	1
8	Impact on gate oxide material of inverted Si^{TM} Junctionless FinFET at 22 nm technology node. , 2017, , .		0
9	Memory Efficient Fractal-SPIHT Based Hybrid Image Encoder. Communications in Computer and Information Science, 2017, , 376-387.	0.5	0
10	Prospects of 2D Junctionless Channel Transistor (JLCT) Towards Analog and RF Metrics Using Si and SiGe in Device Layer. Journal of Low Power Electronics, 2017, 13, 536-544.	0.6	0